

an EL layer comprising an organic material provided over said insulated gate field effect transistor;

a bed plate and a cover plate formed of an insulating material;

a packing material for bonding the bed and cover plates,

wherein the single crystal semiconductor substrate is held in a vacant space which is defined by the bed plate and the cover plate and the packing material, wherein the vacant space is filled with an inert gas and a drying agent,

and

wherein said single crystal semiconductor substrate is fixed over said bed

plate.

3. (Amended) An active matrix type organic EL display device comprising:

an insulated gate field effect transistor provided in a pixel section on a single crystal semiconductor substrate;

an EL layer comprising an organic material provided over said insulated gate field effect transistor;

a bed plate and a cover plate formed of an insulating material;

a packing material for bonding the bed and cover plates,

wherein the single crystal semiconductor substrate is held in a vacant space which is defined by the bed plate and the cover plate and the packing material,

wherein the cover plate comprises a transparent material in a region of the cover plate overlapping with the pixel section,

wherein the vacant space is filled with an inert gas and a drying agent,

and

wherein said single crystal semiconductor substrate is fixed over said bed

plate.

5. (Amended) An active matrix type organic EL display device comprising:

an insulated gate field effect transistor provided in a pixel section on a single crystal semiconductor substrate;

an EL layer comprising an organic material provided over said insulated gate field effect transistor;

a bed plate and a cover plate formed of a ceramics material;

a packing material for bonding the bed and cover plates,

wherein the single crystal semiconductor substrate is held in a vacant space which is defined by the bed plate and the cover plate and the packing material,

wherein the cover plate comprises a transparent material in a region of the cover plate overlapping with the pixel section,

wherein the vacant space is filled with an inert gas selected from the group consisting of helium, argon, krypton, xenon and nitrogen, and is filled with a drying agent selected from the group consisting of barium oxide and silica gel, and

wherein said single crystal semiconductor substrate is fixed over said bed plate.

7. (Amended) An active matrix type organic EL display device comprising:
an insulated gate field effect transistor provided on a single crystal semiconductor substrate;

an EL layer comprising an organic material provided over said insulated gate field effect transistor;

a bed plate and a cover plate formed of an insulating material;

a binder layer for bonding the bed and cover plates,

wherein the single crystal semiconductor substrate is held in a vacant space which is defined by the bed plate and the cover plate and the binder layer,

wherein the vacant space is filled with an inert gas and a drying agent,

and

wherein said single crystal semiconductor substrate is fixed over said bed plate.

9. (Amended) An active matrix type organic EL display device comprising:
an insulated gate field effect transistor provided in a pixel section on a single crystal semiconductor substrate;

an EL layer comprising an organic material provided over said insulated gate field effect transistor;

a bed plate and a cover plate formed of an insulating material;

a binder layer for bonding the bed and cover plates,

wherein the single crystal semiconductor substrate is held in a vacant space which is defined by the bed plate and the cover plate and the binder layer,

wherein the cover plate comprises a transparent material in a region of the cover plate overlapping with the pixel section,

wherein the vacant space is filled with an inert gas and a drying agent,

and

wherein said single crystal semiconductor substrate is fixed over said bed plate.

11. (Amended) An active matrix type organic EL display device comprising:
an insulated gate field effect transistor provided in a pixel section on a single crystal semiconductor substrate;

an EL layer comprising an organic material provided over said insulated gate field effect transistor;

a bed plate and a cover plate formed of a ceramics material;

a binder layer for bonding the bed plate and the cover plates,

wherein the single crystal semiconductor substrate is held in a vacant space which is defined by the bed plate and the cover plate and the binder layer,

wherein the cover plate comprises a transparent material in a region of the cover plate overlapping with the pixel section,

wherein the vacant space is filled with an inert gas selected from the group consisting of helium, argon, krypton, xenon and nitrogen, and is filled with a drying agent selected from the group consisting of barium oxide and silica gel, and

wherein said single crystal semiconductor substrate is fixed over said bed plate.